

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: MMO75-12IO1
Manufacturer: Vishay General Semiconductor - Diodes Division
Package: 8-PACE-PAK
Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/vishay-general-semiconductor-diodes-division/mmo75-12io1.html>

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New & Original Components

Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

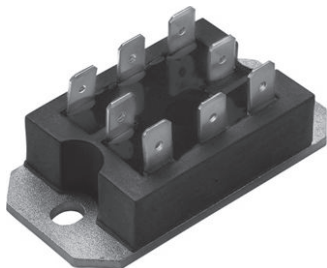
Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Power Modules, Passivated Assembled Circuit Elements, 25 A


PACE-PAK (D-19)

FEATURES

- Glass passivated junctions for greater reliability
- Electrically isolated base plate
- Available up to 1200 V_{RRM}/V_{DRM}
- High dynamic characteristics
- Wide choice of circuit configurations
- Simplified mechanical design and assembly
- UL E78996 approved 
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

DESCRIPTION

The VS-P100 series of integrated power circuits consists of power thyristors and power diodes configured in a single package. With its isolating base plate, mechanical designs are greatly simplified giving advantages of cost reduction and reduced size.

Applications include power supplies, control circuits and battery chargers.

PRIMARY CHARACTERISTICS

I_O	25 A
Type	Modules - thyristor, standard
Package	PACE-PAK (D-19)

MAJOR RATINGS AND CHARACTERISTICS

SYMBOL	CHARACTERISTICS	VALUES	UNITS
I_O	85 °C	25	A
I_{TSM}	50 Hz	357	A
	60 Hz	375	
I^2t	50 Hz	637	A ² s
	60 Hz	580	
$I^2\sqrt{t}$		6365	A ² √s
V_{DRM}, V_{RRM}		400 to 1200	V
V_{ISOL}		2500	V
T_J	Range	-40 to +125	°C
T_{Stg}		-40 to +125	°C

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER	V_{RRM}/V_{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND PEAK OFF-STATE VOLTAGE V	V_{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I_{RRM} MAXIMUM AT T_J MAXIMUM mA
VS-P101, VS-P121, VS-P131	400	500	10
VS-P102, VS-P122, VS-P132	600	700	
VS-P103, VS-P123, VS-P133	800	900	
VS-P103, VS-P124, VS-P134	1000	1100	
VS-P105, VS-P125, VS-P135	1200	1300	



ON-STATE CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum DC output current at case temperature	I _O	Full bridge			25	A
					85	°C
Maximum peak, one-cycle non-repetitive on-state or forward current	I _{TSM} , I _{FSM}	t = 10 ms	No voltage reapplied	Sinusoidal half wave, initial T _J = T _J maximum	357	A
		t = 8.3 ms			375	
		t = 10 ms	100 % V _{RRM} reapplied		300	
		t = 8.3 ms			315	
Maximum I ² t for fusing	I ² t	t = 10 ms	No voltage reapplied		637	A ² s
		t = 8.3 ms			580	
		t = 10 ms	100 % V _{RRM} reapplied		450	
		t = 8.3 ms			410	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to 10 ms, no voltage reapplied I ² t for time tx = I ² √t · √tx			6365	A ² √s
Maximum value of threshold voltage	V _{T(TO)}	T _J = 125 °C			0.82	V
Maximum level value of on-state slope resistance	r _{t1}	T _J = 125 °C, average power = V _{T(TO)} × I _{T(AV)} + r _t + (I _{T(RMS)}) ²			12	mΩ
Maximum on-state voltage drop	V _{TM}	I _{TM} = π × I _{T(AV)}		T _J = 25 °C	1.35	V
Maximum forward voltage drop	V _{FM}	I _{FM} = π × I _{F(AV)}		T _J = 25 °C	1.35	V
Maximum non-repetitive rate of rise of turned-on current	di/dt	T _J = 125 °C from 0.67 V _{DRM} I _{TM} = π × I _{T(AV)} , I _g = 500 mA, t _r < 0.5 μs, t _p > 6 μs			200	A/μs
Maximum holding current	I _H	T _J = 25 °C anode supply = 6 V, resistive load, gate open			130	mA
Maximum latching current	I _L	T _J = 25 °C anode supply = 6 V, resistive load			250	

BLOCKING					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES UNITS
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = 125\text{ °C}$, exponential to 0.67 V_{DRM} gate open			200 $V/\mu s$
Maximum peak reverse and off-state leakage current at V_{RRM}, V_{DRM}	I_{RRM}, I_{DRM}	$T_J = 125\text{ °C}$, gate open circuit			10 mA
Maximum peak reverse leakage current	I_{RRM}	$T_J = 25\text{ °C}$			100 μA
RMS isolation voltage	V_{ISOL}	50 Hz, circuit to base, all terminals shorted, $T_J = 25\text{ °C}$, $t = 1\text{ s}$			2500 V

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum peak gate power	P _{GM}			8	W	
Maximum average gate power	P _{G(AV)}			2		
Maximum peak gate current	I _{GM}			2	A	
Maximum peak negative gate voltage	-V _{GM}			10	V	
Maximum gate voltage required to trigger	V _{GT}	T _J = -40 °C	Anode supply = 6 V resistive load	3	V	
		T _J = 25 °C		2		
		T _J = 125 °C		1		
Maximum gate current required to trigger	I _{GT}	T _J = -40 °C		90	mA	
		T _J = 25 °C		60		
		T _J = 125 °C		35		
Maximum gate voltage that will not trigger	V _{GD}	T _J = 125 °C, rated V _{DRM} applied		0.2	V	
Maximum gate current that will not trigger	I _{GD}			2	mA	



THERMAL AND MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction operating and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case per junction	R_{thJC}	DC operation	2.24	K/W
Maximum thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth and greased	0.10	
Mounting torque, base to heatsink ⁽¹⁾			4	Nm
Approximate weight			58	g
			2.0	oz.
Case style			PACE-PAK (D-19)	

Note

(1) A mounting compound is recommended and the torque should be checked after a period of 3 hours to allow for the spread of the compound

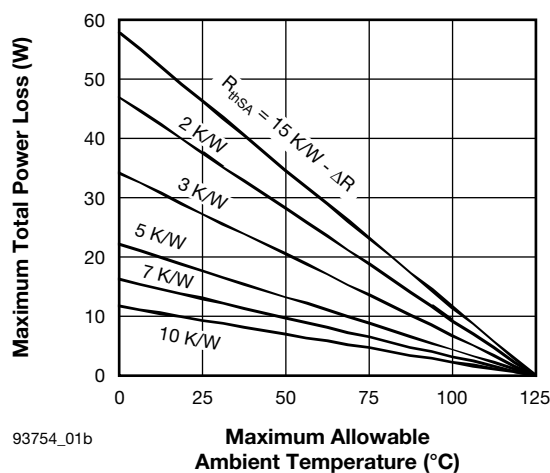
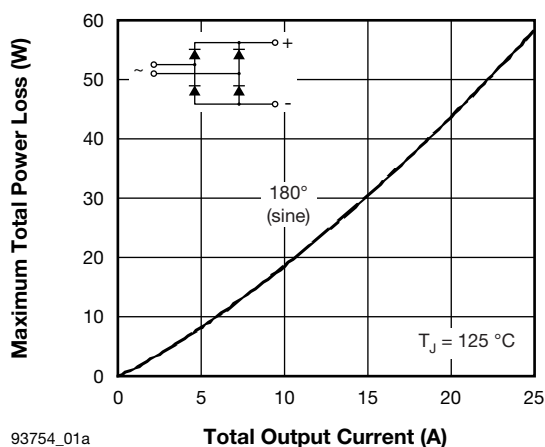


Fig. 1 - Current Ratings Nomogram (1 Module Per Heatsink)

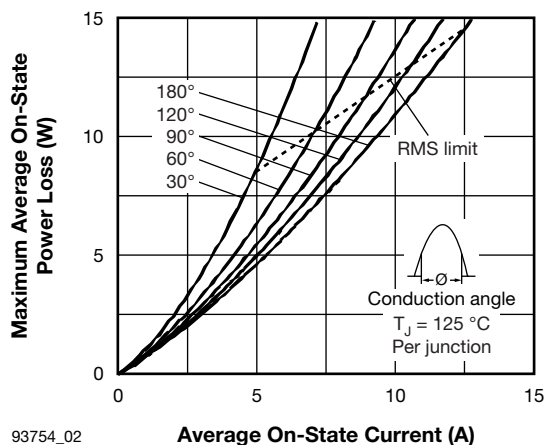


Fig. 2 - On-State Power Loss Characteristics

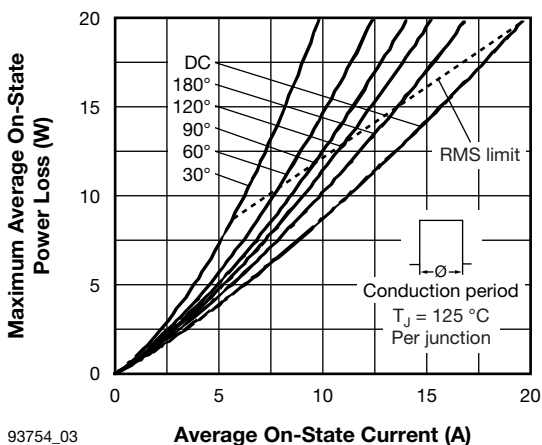


Fig. 3 - On-State Power Loss Characteristics

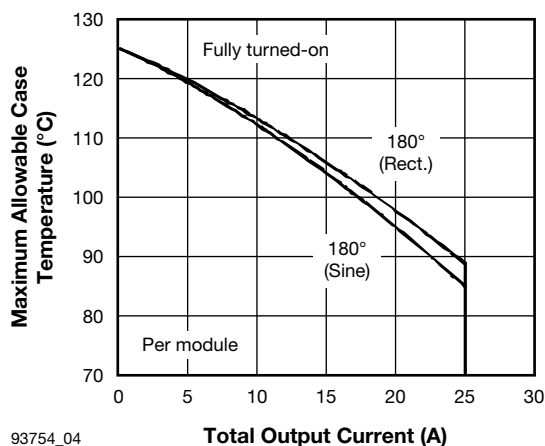


Fig. 4 - Current Ratings Characteristics

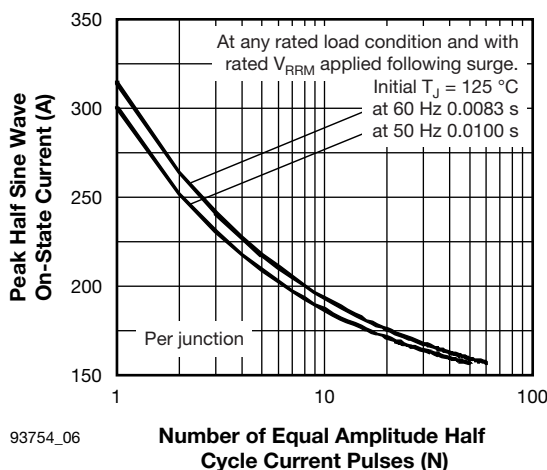


Fig. 6 - Maximum Non-Repetitive Surge Current

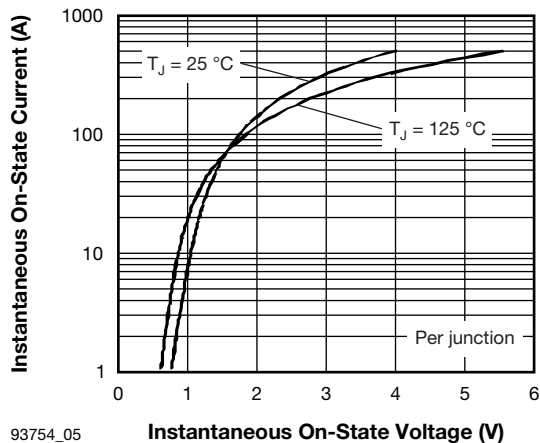


Fig. 5 - On-State Voltage Drop Characteristics

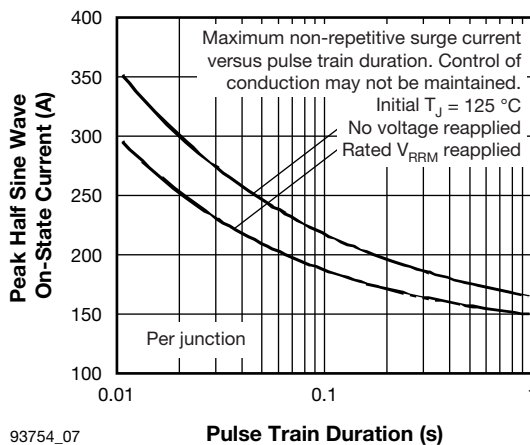
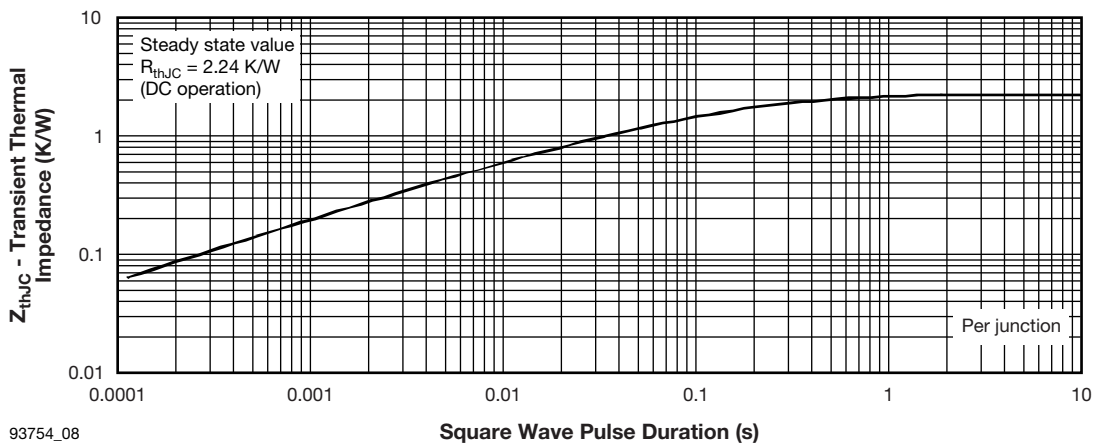


Fig. 7 - Maximum Non-Repetitive Surge Current


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

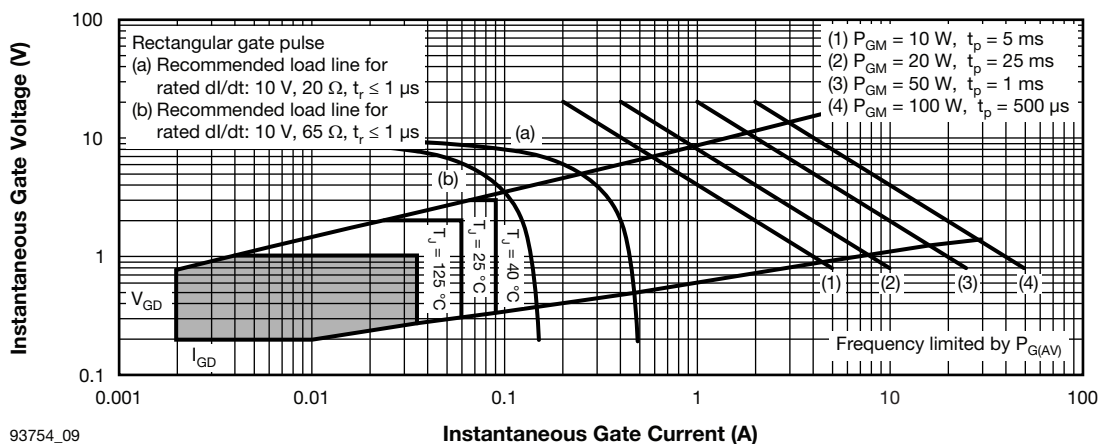


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

Device code

VS-	P	1	0	2	K	W
①	②	③	④	⑤	⑥	⑦

- 1** - Vishay Semiconductors product
- 2** - Module type
- 3** - Current rating
1 = 25 A DC (P100 series)
4 = 40 A DC (P400 series)
- 4** - Circuit configuration
0 = single phase, hybrid bridge common cathode
2 = single phase, hybrid bridge doubler connection
3 = single phase, all SCR Bridge
- 5** - Voltage code
1 = 400 V
2 = 600 V
3 = 800 V
4 = 1000 V
5 = 1200 V
- 6** - K = optional voltage suppression
- 7** - W = optional freewheeling diode

CIRCUIT CONFIGURATION			
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	SCHEMATIC DIAGRAM	TERMINAL POSITIONS
Single phase, hybrid bridge common cathode	0		
Single phase, hybrid bridge doubler connection	2		
Single phase, all SCR bridge	3		

CODING ⁽¹⁾					
CIRCUIT DESCRIPTION	CIRCUIT CONFIGURATION CODE	BASIC SERIES	WITH VOLTAGE SUPPRESSION	WITH FREEWHEELING DIODE	WITH BOTH VOLTAGE SUPPRESSION AND FREEWHEELING DIODE
Single phase, hybrid bridge common cathode	0	P10.	P10.K	P10.W	P10.KW
Single phase, hybrid bridge doubler connection	2	P12.	P12.K	-	-
Single phase, all SCR bridge	3	P13.	P13.K	-	-

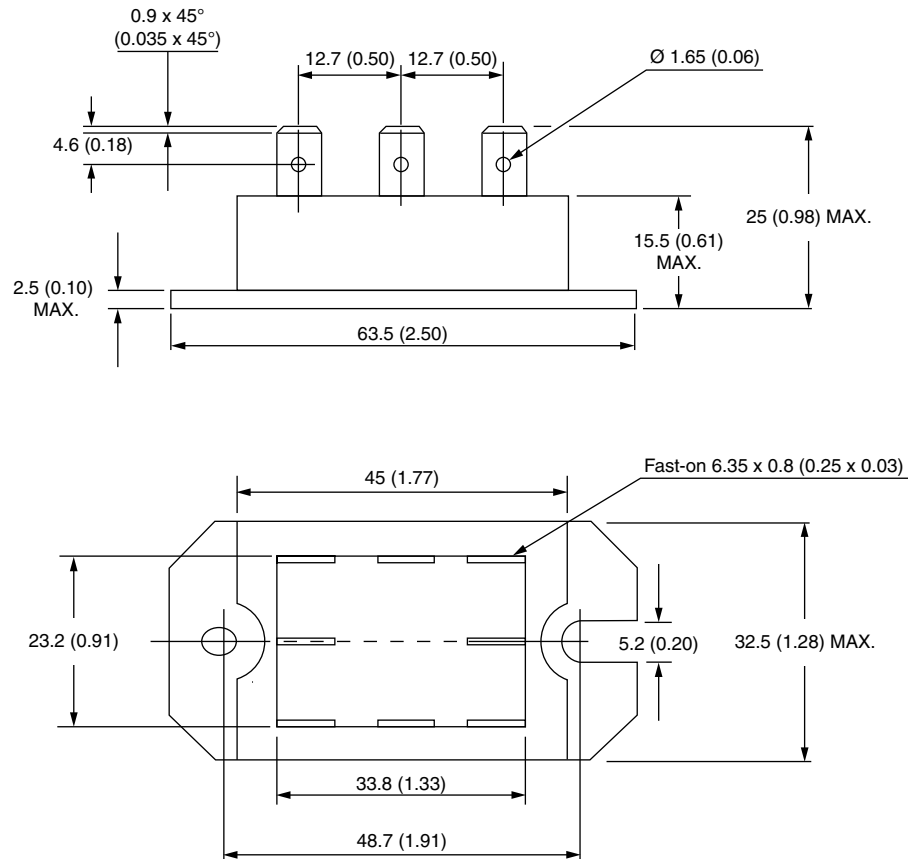
Note

⁽¹⁾ To complete code refer to Voltage Ratings table, i.e.: for 600 V P10.W complete code is P102W

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95335

D-19 PACE-PAK

DIMENSIONS in millimeters (inches)





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